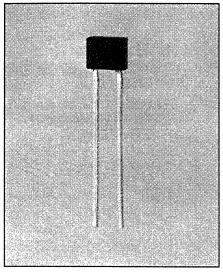
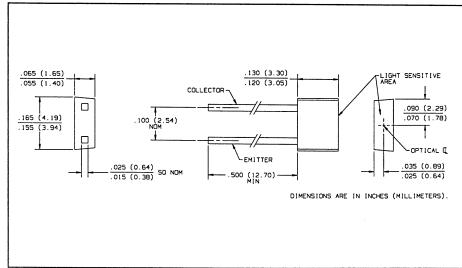


NPN Silicon Phototransistors Types OP508FA, OP508FB, OP508FC





Features

- Flat lensed for wide acceptance angle
- Easily stackable on 0.100 inch (2.54 mm) hole centers
- Low cost plastic package
- Mechanically and spectrally matched to the OP168F and OP268F series of infrared emitting diodes

Description

The OP508F series consist of NPN silicon phototransistors mounted in flat, black plastic, "end looking" packages. The flat sensing surface allows an acceptance half angle of 60° measured from the optical axis to the half power point. The black plastic package significantly reduces ambient light noise. These devices can be mounted on 0.100" (2.54 mm) hole centers, making them an ideal low cost alternate to hermetic OP600 sensors.

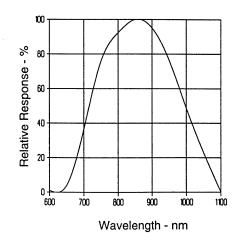
Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

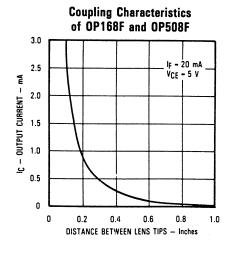
Collector-Emitter Voltage
Emitter-Collector Voltage 5.0 V
Storage and Operating Temperature Range
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering
iron] 260° Č ⁽¹⁾
Power Dissipation 100 mW ⁽²⁾
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering. Maximum 20 grams force may be applied to the leads when soldering. (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) To calculate typical collector dark current in μA , use the formula $I_{CEO} = 10^{(0.040T_A-3.4)}$ where TA is ambient temperature in ° C.

Typical Performance Curves

Typical Spectral Response



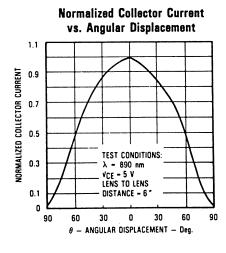


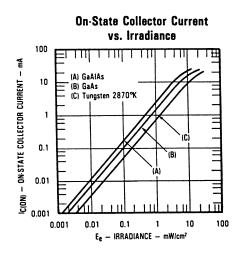
Types OP508FA, OP508FB, OP508FC

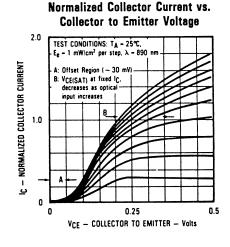
Electrical Characteristics (T_A = 25° C unless otherwise noted)

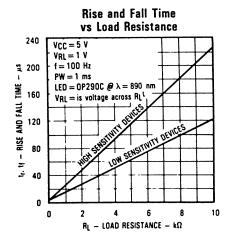
SYMBOL	PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITIONS
IC(ON)	On-State Collector Current	OP508FC OP508FB OP508FA	0.34 0.65 2.70		5.10	mA	$V_{CE} = 5.0 \text{ V, } E_e = 5 \text{ mW/cm}^{2(3)}$
Ις/ΔΤ	Relative I _C Change with Temperature			1.00		%/°C	$V_{CE} = 5.0 \text{ V},$ $E_e = 1.0 \text{ mW/cm}^{2(3)}, \lambda = 890 \text{ nm}$
ICEO	Collector-Dark Current				100	nA	$V_{CE} = 10.0 \text{ V}, E_e = 0^{(4)}$
V _(BR) CEO	Collector-Emittor Breakdown Voltage		30			V	I _C = 100 μA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage		5.0			V	I _E = 100 μA
V _{CE(SAT)}	Collector-Emitter Saturation Volta	ige			0.40	V	$I_C = 100 \mu\text{A}, E_e = 5 \text{mW/cm}^{2(3)}$

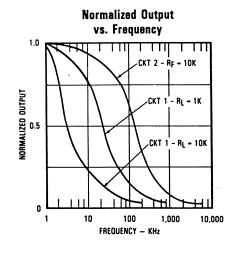
Typical Performance Curves

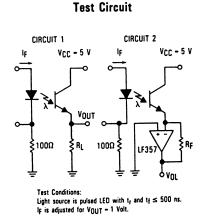












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